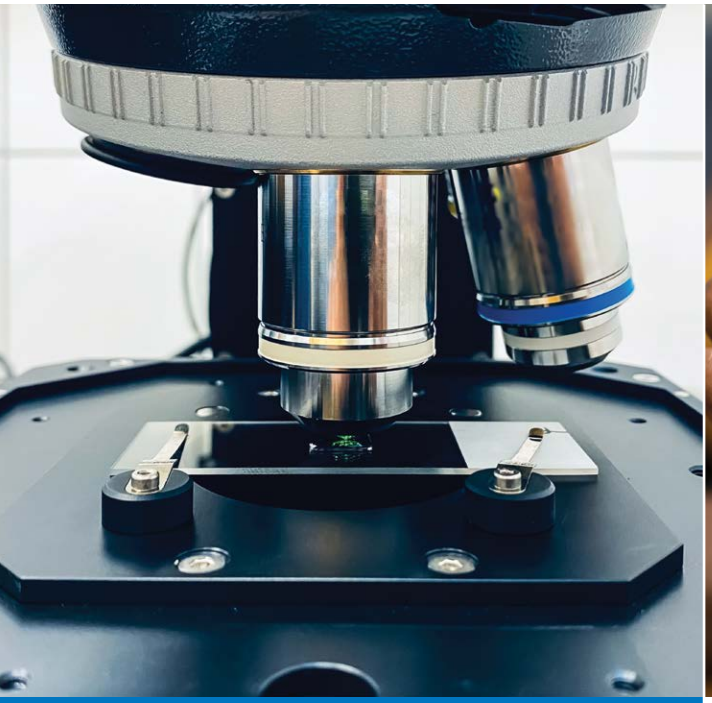
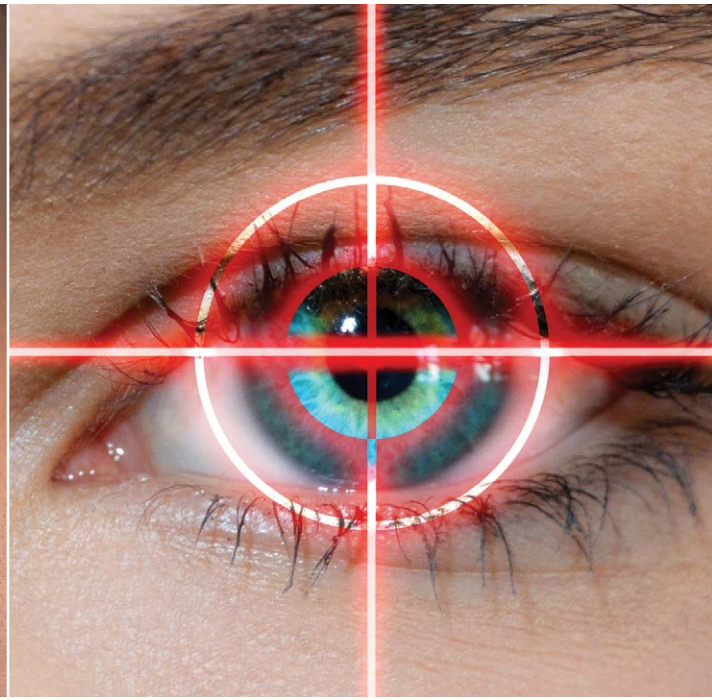
TELEDYNE

Teledyne Judson Technologies

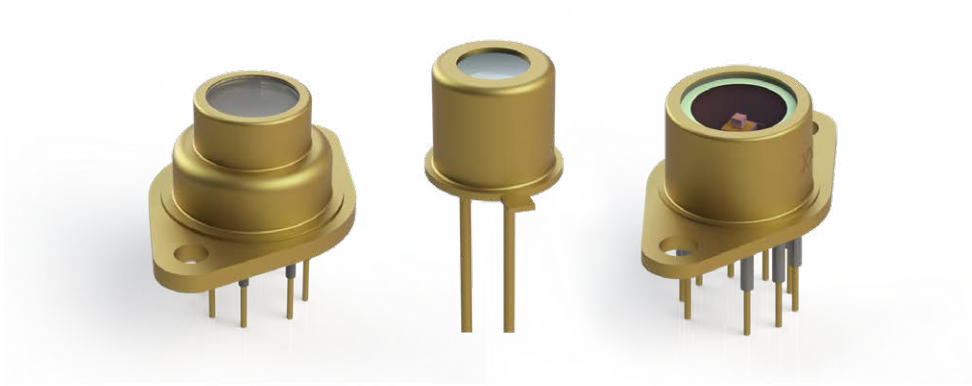
InGaAs Detectors

A Guide to InGaAs and Extended InGaAs Detectors





Room Temperature: 1.7–2.6 µm
TE Cooled: 1.7–2.6 µm
Quads and Linear Arrays



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UNMATCHED PERFORMANCE
InGaAs Sensors for Advanced Applications

Teledyne Judson Technologies' InGaAs sensors operate with a cut-off wavelength from 1.7 µm to 2.6 µm, making them versatile for applications like clinical analyzers, NIR-FTIR, Raman spectroscopy, optical communication, and currency validation. These sensors offer enhanced sensitivity, superior quantum efficiency, and minimal dark current providing researchers and engineers with advanced capabilities to tackle photonic challenges.

KEY TECHNOLOGY FEATURES & APPLICATIONS

Features

- Stable response vs. temperature
- Wide dynamic range
- High linearity
- No bias or cooling required
- Can be ordered integrated with an amplifier and TE controller for easy integration

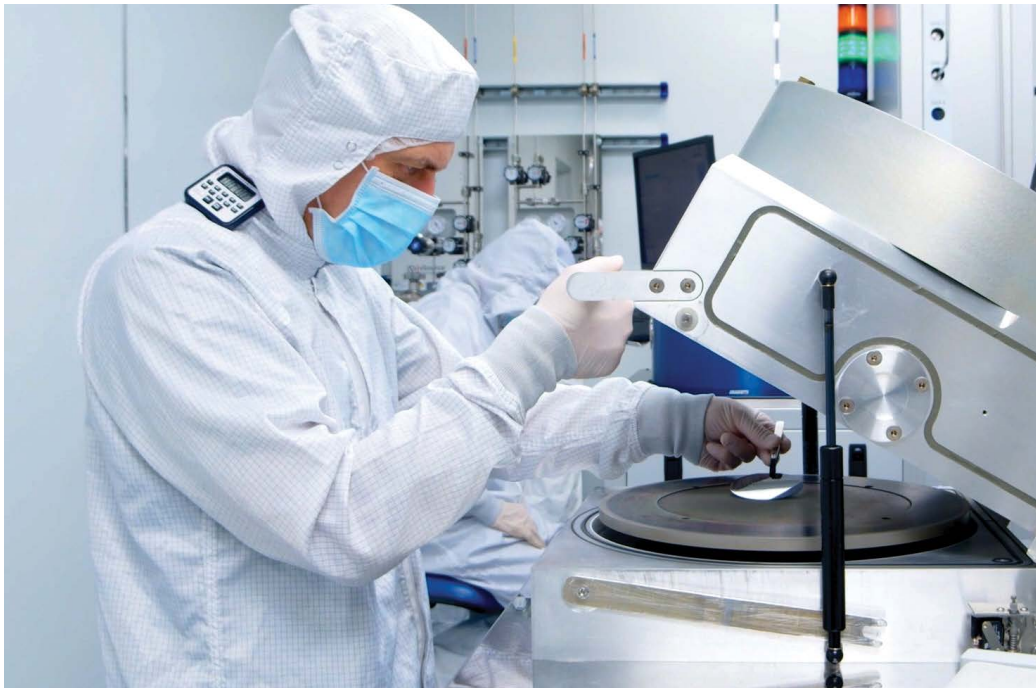
Applications

- Gas analysis
- NIR-FTIR
- Raman spectroscopy
- IR fluorescence
- Blood analysis
- Optical Sorting
- Radiometry
- Chemical detection
- Optical communication
- Optical power monitoring
- Laser diode monitoring
- Laser burn-in

CUSTOM DESIGN SERVICES

For more demanding applications, Teledyne's team of engineers will provide custom design services. Custom products are available in standard TO packages, TE cooled, LN2 cooled, and bare die. We also offer different window materials, lenses or optical filter options.

Please contact us with your special requirements.



TELEDYNE

Teledyne Judson Technologies

InGaAs Detectors

A Guide to InGaAs (J22 series) and Extended InGaAs (J23 series) Detectors

General

The **J22 and J23 series** are high-performance Indium Gallium Arsenide (InGaAs) detectors that operate over a spectral range from 1.7 µm to 2.6 µm. These detectors provide fast rise time, uniform response, excellent sensitivity, and long-term reliability for a wide range of applications.

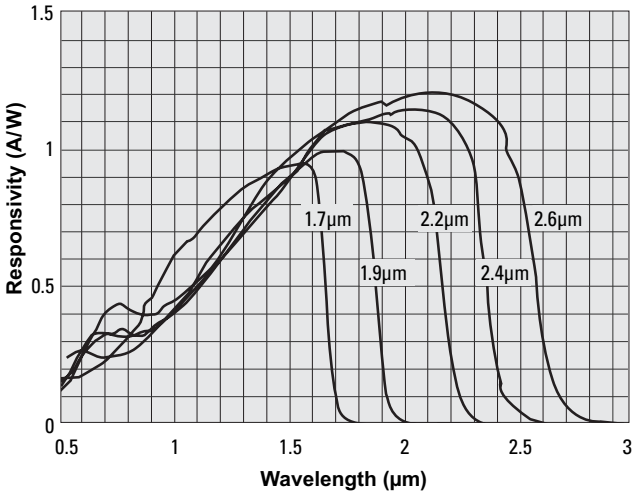
For enhanced performance or temperature stability near the cutoff wavelength, Teledyne offers various thermoelectrically cooled detector options.

Device Options

Teledyne's standard InGaAs detectors, the **J22 series**, offer high reliability and performance in the spectral range from 0.8 µm to 1.7 µm. Additionally, the **J23 series** extended InGaAs detectors are available with four cutoff options at 1.9 µm, 2.2 µm, 2.4 µm, and 2.6 µm.

The diagram below shows the typical response for the J22 and J23 series at room temperature operation.

Responsivity vs. Wavelength for InGaAs at 22°C



Package Options

The **J22 and J23 series** are available in standard TO packages, ceramic sub-mounts, and bare die. TO packages are a type of housing for electronic components, while ceramic sub-mounts provide a stable base for the detectors. Bare die refers to the detector without any packaging. We also offer different window materials, lenses, or optical filter options to enhance the detector's performance by modifying the light that reaches it.

For more demanding applications, Teledyne Judson's team of engineers can provide custom design services. Please contact us with your special requirements.

Accessories

For a complete system, Teledyne's team offers low-noise transimpedance amplifier modules, which convert current to voltage with low noise, heat sink/preamp assemblies to manage heat and amplify signals, and temperature controllers to maintain the detector's optimal operating temperature.

For further details, please visit our website.

InGaAs

ROOM TEMPERATURE SENSORS

Description	Active Size Diameter (mm)	Operating Temperature	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Dark Current (A) @ V r (max) typ	Peak D* (cm Hz^1/2 / W) @ 1K Hz typ	NE P (W/r t-Hz) @ peak wavelength typ
J22-18I-R40U-1.7	0.04	22	1.7	1.65	0.9	18I	1.50E+09	3.00E-11	1.00E+12	3.50E-15
J22-18I-R75U-1.7	0.075	22	1.7	1.65	0.9		1.00E+09	4.00E-11	1.50E+12	4.50E-15
J22-18I-R250U-1.7	0.25	22	1.7	1.65	0.9		6.00E+08	1.00E-10	3.80E+12	5.80E-15
J22-18I-R500U-1.7	0.5	22	1.7	1.65	0.9		2.00E+08	2.50E-10	4.40E+12	1.00E-14
J22-18I-R01M-1.7	1	22	1.7	1.65	0.9		6.00E+07	1.00E-09	4.80E+12	1.80E-14
J22-5I-R02M-1.7	2	22	1.7	1.65	0.9	5I	1.60E+07	4.00E-09	5.00E+12	3.50E-14
J22-5I-R03M-1.7	3	22	1.7	1.65	0.9		6.00E+06	1.00E-07	4.6E+12	6E-14
J22-8I-R05M-1.7	5	22	1.7	1.65	0.9	8I	2.00E+06	1.00E-07	4.4E+12	5.5E-14
J23-18I-R250U-1.9	0.25	22	1.9	1.75	1	18I	1.60E+07	1.00E-08	6.90E+11	3.20E-14
J23-18I-R500U-1.9	0.5	22	1.9	1.75	1		5.20E+06	3.00E-08	7.90E+11	5.60E-14
J23-18I-R01M-1.9	1	22	1.9	1.75	1		1.60E+06	1.00E-07	8.80E+11	1.00E-13
J23-5I-R02M-1.9	2	22	1.9	1.75	1	5I	3.00E+05	4.00E-07	7.60E+11	2.30E-13
J23-5I-R03M-1.9	3	22	1.9	1.75	1		9.00E+04	1.00E-06	6.30E+11	4.30E-13
J23-18I-R250U-2.2	0.25	22	2.2	1.9	1.1	18I	1.00E+06	1.00E-07	1.90E+11	1.20E-13
J23-18I-R500U-2.2	0.5	22	2.2	1.9	1.1		3.40E+05	3.00E-07	2.20E+11	2.00E-13
J23-18I-R01M-2.2	1	22	2.2	1.9	1.1		1.00E+05	1.00E-06	2.40E+11	3.70E-13
J23-5I-R02M-2.2	2	22	2.2	1.9	1.1	5I	2.00E+04	4.00E-06	2.20E+11	8.20E-13
J23-5I-R03M-2.2	3	22	2.2	1.9	1.1		6.00E+03	1.00E-05	1.80E+11	1.50E-12
J23-18I-R250U-2.4	0.25	22	2.4	2.15	1.15	18I	2.00E+05	3.50E-07	8.90E+10	2.50E-13
J23-18I-R500U-2.4	0.5	22	2.4	2.15	1.15		6.60E+04	1.00E-06	1.00E+11	4.30E-13
J23-18I-R01M-2.4	1	22	2.4	2.15	1.15		2.00E+04	3.50E-06	1.10E+11	7.80E-13
J23-5I-R02M-2.4	2	22	2.4	2.15	1.15	5I	4.00E+03	1.50E-05	1.00E+11	1.80E-12
J23-5I-R03M-2.4	3	22	2.4	2.15	1.1		1.30E+03	3.50E-05	8.30E+10	3.20E-12
J23-18I-R250U-2.6	0.25	22	2.6	2.25	1.2	18I	5.00E+04	1.00E-06	4.70E+10	4.80E-13
J23-18I-R500U-2.6	0.5	22	2.6	2.25	1.2		1.60E+04	3.00E-06	5.30E+10	8.40E-13
J23-18I-R01M-2.6	1	22	2.6	2.25	1.2		5.00E+03	1.00E-05	5.90E+10	1.50E-12
J23-5I-R02M-2.6	2	22	2.6	2.25	1.2	5I	1.00E+03	4.00E-05	5.30E+10	3.40E-12
J23-5I-R03M-2.6	3	22	2.6	2.25	1.1		3.20E+02	1.00E-04	4.10E+10	6.50E-12

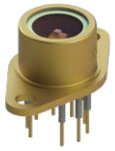
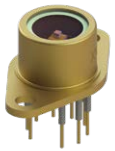
InGaAs

COOLED SENSORS

Description	Material	Active Size Diameter (mm)	Operating Temperature °C	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Capacitance (pF) @ 0V typ	Peak D* (cm Hz^1/2 / W) @ 1K Hz typ	NE P (W/r t-Hz) @ peak wavelength typ
J22TE1-66C-R500U-1.7	InGaAs	0.5	-20	1.63	0.9	66C	8.00E+09	25	3E+13	1.5E-15
J22TE1-66C-R01M-1.7	InGaAs	1	-20	1.63	0.9		3.00E+09	125	3.7E+13	2.4E-15
J22TE1-66C-R02M-1.7	InGaAs	2	-20	1.63	0.9		7.20E+08	500	3.6E+13	4.9E-15
J22TE1-66C-R03M-1.7	InGaAs	3	-20	1.63	0.9		2.60E+08	1200	3.3E+13	8.1E-15
J22TE1-66C-R05M-1.7	InGaAs	5	-20	1.63	0.9		8.00E+07	3200	3E+13	1.5E-14
J22TE2-66C-R01M-1.7	InGaAs	1	-40	1.62	0.9		2.00E+10	125	9.9E+13	8.9E-16
J22TE2-66C-R02M-1.7	InGaAs	2	-40	1.62	0.9		4.40E+09	500	9.3E+13	1.9E-15
J22TE2-66C-R03M-1.7	InGaAs	3	-40	1.62	0.9		1.60E+09	1200	8.4E+13	3.2E-15
J22TE2-66C-R05M-1.7	InGaAs	5	-40	1.62	0.9		4.80E+08	3200	7.7E+13	5.8E-15
J22TE3-66C-R01M-1.7	InGaAs	1	-65	1.6	0.9		2.00E+11	125	3.4E+14	2.65E-16
J22TE3-66C-R03M-1.7	InGaAs	3	-65	1.6	0.9		1.40E+10	1200	2.6E+14	1E-15
J22TE4-3CN-R500U-1.7	InGaAs	0.5	-85	1.59	0.9	3CN	2.40E+12	25	6E+14	7.5E-17
J23TE1-66C-R250U-1.9	InGaAs	0.25	-20	1.85	1	66C	5.60E+08	75	4.4E+12	5E-15
J23TE1-66C-R500U-1.9	InGaAs	0.5	-20	1.85	1		2.00E+08	250	5.3E+12	8.4E-15
J23TE1-66C-R01M-1.9	InGaAs	1	-20	1.85	1		6.00E+07	1000	5.80E+12	1.50E-14
J23TE1-66C-R02M-1.9	InGaAs	2	-20	1.85	1		1.10E+07	4000	5.00E+12	3.60E-14
J23TE1-66C-R03M-1.9	InGaAs	3	-20	1.85	1		3.00E+06	9000	3.90E+12	6.80E-14
J23TE2-66C-R250U-1.9	InGaAs	0.25	-40	1.83	1		2.80E+09	75	1.00E+13	2.10E-15
J23TE2-66C-R500U-1.9	InGaAs	0.5	-40	1.83	1		1.00E+09	250	1.30E+13	3.50E-15
J23TE2-66C-R01M-1.9	InGaAs	1	-40	1.83	1		3.20E+08	1000	1.40E+13	6.30E-15
J23TE2-66C-R02M-1.9	InGaAs	2	-40	1.83	1		5.20E+07	4000	1.10E+13	1.60E-14
J23TE2-66C-R03M-1.9	InGaAs	3	-40	1.83	1		1.50E+07	9000	9.10E+12	2.90E-14
J23TE3-66C-R250U-1.9	InGaAs	0.25	-65	1.82	1		1.60E+10	75	2.60E+13	8.50E-16
J23TE3-66C-R500U-1.9	InGaAs	0.5	-65	1.82	1		7.00E+09	250	3.50E+13	1.30E-15
J23TE3-66C-R01M-1.9	InGaAs	1	-65	1.82	1		2.40E+09	1000	4.10E+13	2.20E-15
J23TE3-66C-R02M-1.9	InGaAs	2	-65	1.82	1		3.40E+08	4000	3.10E+13	5.80E-15
J23TE3-66C-R03M-1.9	InGaAs	3	-65	1.82	1		8.00E+07	9000	2.20E+13	1.20E-14
J23TE4-3CN-R250U-1.9	InGaAs	0.25	-85	1.81	1	3CN	6.40E+10	75	5.50E+13	4.00E-16
J23TE4-3CN-R500U-1.9	InGaAs	0.5	-85	1.81	1		3.20E+10	250	7.80E+13	5.70E-16
J23TE4-3CN-R01M-1.9	InGaAs	1	-85	1.81	1		1.20E+10	1000	9.50E+13	9.30E-16
J23TE4-3CN-R02M-1.9	InGaAs	2	-85	1.81	1		1.40E+09	4000	6.50E+13	2.70E-15

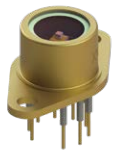
InGaAs

COOLED SENSORS continued

Description	Material	Active Size Diameter (mm)	Operating Temperature °C	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Capacitance (pF) @ 0V typ	Peak D* (cm Hz^1/2 / W) @ 1K Hz typ	NE P (W/r t-Hz) @ peak wavelength typ
J23TE4-3CN-R03M-1.9	InGaAs	3	-85	1.81	1	3CN	3.00E+08	9000	4.50E+13	5.90E-15
J23TE1-66C-R250U-2.2	InGaAs	0.25	-20	2.14	1.1	66C	2.20E+07	75	9.70E+11	2.30E-14
J23TE1-66C-R500U-2.2	InGaAs	0.5	-20	2.14	1.1		8.00E+06	250	1.20E+12	3.80E-14
J23TE1-66C-R01M-2.2	InGaAs	1	-20	2.14	1.1		2.40E+06	1000	1.30E+12	6.90E-14
J23TE1-66C-R02M-2.2	InGaAs	2	-20	2.14	1.1		4.40E+05	4000	1.10E+12	1.60E-13
J23TE1-66C-R03M-2.2	InGaAs	3	-20	2.14	1.1		1.20E+05	9000	8.70E+11	3.10E-13
J23TE2-66C-R250U-2.2	InGaAs	0.25	-40	2.11	1.1		9.60E+07	75	2.10E+12	1.10E-14
J23TE2-66C-R500U-2.2	InGaAs	0.5	-40	2.11	1.1		3.60E+07	250	2.60E+12	1.70E-14
J23TE2-66C-R01M-2.2	InGaAs	1	-40	2.11	1.1		1.10E+07	1000	2.90E+12	3.10E-14
J23TE2-66C-R02M-2.2	InGaAs	2	-40	2.11	1.1		1.90E+06	4000	2.40E+12	7.50E-14
J23TE2-66C-R03M-2.2	InGaAs	3	-40	2.11	1.1		5.20E+05	9000	1.90E+12	1.40E-13
J23TE3-66C-R250U-2.2	InGaAs	0.25	-65	2.09	1.1		5.20E+08	75	5.20E+12	4.30E-15
J23TE3-66C-R500U-2.2	InGaAs	0.5	-65	2.09	1.1		2.20E+08	250	6.70E+12	6.60E-15
J23TE3-66C-R01M-2.2	InGaAs	1	-65	2.09	1.1		7.00E+07	1000	7.60E+12	1.40E-14
J23TE3-66C-R02M-2.2	InGaAs	2	-65	2.09	1.1		1.10E+07	4000	6.00E+12	2.90E-14
J23TE3-66C-R03M-2.2	InGaAs	3	-65	2.09	1.1		2.60E+06	9000	4.40E+12	6.00E-14
J23TE4-3CN-R250U-2.2	InGaAs	0.25	-85	2.07	1.1	3CN	1.90E+09	75	1.00E+13	2.10E-15
J23TE4-3CN-R500U-2.2	InGaAs	0.5	-85	2.07	1.1		9.00E+08	250	1.40E+13	3.10E-15
J23TE4-3CN-R01M-2.2	InGaAs	1	-85	2.07	1.1		3.00E+08	1000	1.70E+13	5.30E-15
J23TE4-3CN-R02M-2.2	InGaAs	2	-85	2.07	1.1		4.20E+07	4000	1.20E+13	1.40E-14
J23TE4-3CN-R03M-2.2	InGaAs	3	-85	2.07	1.1		9.00E+06	9000	8.60E+12	3.10E-14
J23TE1-66C-R250U-2.4	InGaAs	0.25	-20	2.34	1.15	66C	5.40E+06	75	5.00E+11	4.40E-14
J23TE1-66C-R500U-2.4	InGaAs	0.5	-20	2.34	1.15		2.00E+06	250	6.10E+11	7.30E-14
J23TE1-66C-R01M-2.4	InGaAs	1	-20	2.34	1.15		6.00E+05	1000	6.70E+11	1.30E-13
J23TE1-66C-R02M-2.4	InGaAs	2	-20	2.34	1.15		1.00E+05	4000	5.50E+11	3.20E-13
J23TE1-66C-R03M-2.4	InGaAs	3	-20	2.34	1.15		3.00E+04	9000	4.50E+11	5.90E-13
J23TE2-66C-R250U-2.4	InGaAs	0.25	-40	2.31	1.15		2.40E+07	75	1.10E+12	2.00E-14
J23TE2-66C-R500U-2.4	InGaAs	0.5	-40	2.31	1.15		9.00E+06	250	1.30E+12	3.30E-14
J23TE2-66C-R01M-2.4	InGaAs	1	-40	2.31	1.15		3.00E+06	1000	1.60E+12	5.70E-14
J23TE2-66C-R02M-2.4	InGaAs	2	-40	2.31	1.15		4.60E+05	4000	1.20E+12	1.50E-13
J23TE2-66C-R03M-2.4	InGaAs	3	-40	2.31	1.15		1.30E+05	9000	9.60E+11	2.80E-13

InGaAs

COOLED SENSORS continued

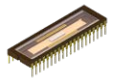
Description	Material	Active Size Diameter (mm)	Operating Temperature °C	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Capacitance (pF) @ 0V typ	Peak D* (cm Hz^1/2 / W) @ 1K Hz typ	NE P (W/r t-Hz) @ peak wavelength typ
J23TE3-66C-R250U-2.4	InGaAs	0.25	-65	2.29	1.15	66C 	9.60E+07	75	2.30E+12	9.50E-15
J23TE3-66C-R500U-2.4	InGaAs	0.5	-65	2.29	1.15		4.40E+07	250	3.20E+12	1.40E-14
J23TE3-66C-R01M-2.4	InGaAs	1	-65	2.29	1.15		1.50E+07	1000	3.70E+12	2.40E-14
J23TE3-66C-R02M-2.4	InGaAs	2	-65	2.29	1.15		2.00E+06	4000	2.70E+12	6.60E-14
J23TE3-66C-R03M-2.4	InGaAs	3	-65	2.29	1.15		5.00E+05	9000	2.00E+12	1.30E-13
J23TE4-3CN-R250U-2.4	InGaAs	0.25	-85	2.27	1.15	3CN 	3.00E+08	7.50E+01	4.30E+12	5.10E-15
J23TE4-3CN-R500U-2.4	InGaAs	0.5	-85	2.27	1.15		1.30E+08	2.50E+02	5.70E+12	7.70E-15
J23TE4-3CN-R01M-2.4	InGaAs	1	-85	2.27	1.15		5.00E+07	1.00E+03	7.10E+12	1.30E-14
J23TE4-3CN-R02M-2.4	InGaAs	2	-85	2.27	1.15		6.20E+06	4.00E+03	5.00E+12	3.60E-14
J23TE4-3CN-R03M-2.4	InGaAs	3	-85	2.27	1.15		1.60E+06	9.00E+03	3.80E+12	7.00E-14
J23TE1-66C-R250U-2.6	InGaAs	0.25	-20	2.52	1.2	66C 	1.40E+06	75	2.70E+11	8.30E-14
J23TE1-66C-R500U-2.6	InGaAs	0.5	-20	2.52	1.2		5.20E+05	250	3.20E+11	1.40E-13
J23TE1-66C-R01M-2.6	InGaAs	1	-20	2.52	1.2		1.60E+05	1000	3.60E+11	2.50E-13
J23TE1-66C-R02M-2.6	InGaAs	2	-20	2.52	1.2		2.60E+04	4000	2.90E+11	6.10E-13
J23TE1-66C-R03M-2.6	InGaAs	3	-20	2.52	1.2		7.00E+03	9000	2.30E+11	1.20E-12
J23TE2-66C-R250U-2.6	InGaAs	0.25	-40	2.48	1.2		6.00E+06	75	5.70E+11	3.90E-14
J23TE2-66C-R500U-2.6	InGaAs	0.5	-40	2.48	1.2		2.60E+06	250	7.60E+11	5.90E-14
J23TE2-66C-R01M-2.6	InGaAs	1	-40	2.48	1.2		8.00E+05	1000	8.40E+11	1.10E-13
J23TE2-66C-R02M-2.6	InGaAs	2	-40	2.48	1.2		1.20E+05	4000	6.50E+11	2.70E-13
J23TE2-66C-R03M-2.6	InGaAs	3	-40	2.48	1.2		3.00E+04	9000	4.90E+11	5.50E-13
J23TE3-66C-R250U-2.6	InGaAs	0.25	-65	2.45	1.2		2.80E+07	75	1.30E+12	1.70E-14
J23TE3-66C-R500U-2.6	InGaAs	0.5	-65	2.45	1.2		1.20E+07	250	1.70E+12	2.60E-14
J23TE3-66C-R01M-2.6	InGaAs	1	-65	2.45	1.2		4.00E+06	1000	2.00E+12	4.50E-14
J23TE3-66C-R02M-2.6	InGaAs	2	-65	2.45	1.2		5.80E+05	4000	1.50E+12	1.20E-13
J23TE3-66C-R03M-2.6	InGaAs	3	-65	2.45	1.2		1.40E+05	9000	1.10E+12	2.40E-13
J23TE4-3CN-R250U-2.6	InGaAs	0.25	-85	2.43	1.2	3CN 	8.00E+07	75	2.30E+12	9.50E-15
J23TE4-3CN-R500U-2.6	InGaAs	0.5	-85	2.43	1.2		3.60E+07	250	3.10E+12	1.40E-14
J23TE4-3CN-R01M-2.6	InGaAs	1	-85	2.43	1.2		1.20E+07	1000	3.60E+12	2.50E-14
J23TE4-3CN-R02M-2.6	InGaAs	2	-85	2.43	1.2		1.70E+06	4000	2.70E+12	6.50E-14
J23TE4-3CN-R03M-2.6	InGaAs	3	-85	2.43	1.2		4.00E+05	9000	2.00E+12	1.30E-13

InGaAs

QUAD ARRAYS

Description	Material	Active Size Diameter (mm)	Operating Temperature °C	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Capacitance (pF) @ 0V typ	Dark Current (A) @ V r (max) typ
J22QUAD-8D6-R02M-1.7	InGaAs	2	-20	1.63	0.9	8D6	3.00E+07	125	1.00E-09
J23QUAD-5I-R02M-2.2	InGaAs	2	22	2.2	1.1	5I	1.00E+05	1000	1.00E-06

LINEAR ARRAYS

Description	Material	Active Size Diameter (mm)	Operating Temperature °C	50% Cutoff Wavelength (µm), ±0.1 µm	Peak Responsivity (A/W) min	Package	Shunt Impedance (Ohm) typ	Capacitance (pF) @ 0V typ	Dark Current (A) @ V r (max) typ	Peak D* (cm Hz^1/2 / W) @ 1K Hz typ	NE P (W/r t-Hz) @ peak wavelength typ
J22P-40P-500UX1M:16E	InGaAs	0.5x1	22	1.7	0.9	40-pin DIP 	8.00E+07	70	5E-10	4.461E+12	1.59E-14
J22P-40P-500UX1M:32E	InGaAs	0.5x1	22	1.7	0.9		8.00E+07	70	5E-10	4.461E+12	1.59E-14
J22P-64P-500UX1M:64E-1.7	InGaAs	0.5x1	22	1.7	0.9		8.00E+07	70	5E-10	4.461E+12	1.59E-14

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